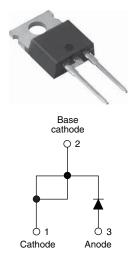
Vishay Semiconductors

HEXFRED[®], Ultrafast Soft Recovery Diode, 6 A



www.vishay.com

TO-220AC

PRODUCT SUMMARY								
Package	TO-220AC							
I _{F(AV)}	6 A							
V _R	1200 V							
V _F at I _F	3.0 V							
t _{rr} (typ.)	26 ns							
T _J max.	150 °C							
Diode variation	Single die							

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified for industrial level

BENEFITS

- Reduced RFI and EMI
 - · Reduced power loss in diode and switching transistor
 - Higher frequency operation
 - Reduced snubbing
 - Reduced parts count

DESCRIPTION

VS-HFA06TB120PbF is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 6 A continuous current, the VS-HFA06TB120PbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RBM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA06TB120PbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V _R		1200	V					
Maximum continuous forward current	I _F	T _C = 100 °C	6						
Single pulse forward current	I _{FSM}		80	А					
Maximum repetitive forward current	I _{FRM}		24						
Maximum power discipation	D-	T _C = 25 °C	62.5	W					
Maximum power dissipation	PD	T _C = 100 °C	25	vv					
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C					

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RoHS

COMPLIANT



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ELECTRIACL SPECIFICATIONS ($T_J = 25 \text{ °C}$ unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	1200	-	-				
Maximum forward voltage		I _F = 6.0 A	-	2.7	3.0	v			
	V _{FM}	I _F = 12 A	-	3.5	3.9)			
		I _F = 6.0 A, T _J = 125 °C	-	2.4	2.8				
Maximum reverse		V _R = V _R rated	-	0.26	5.0				
leakage current	IRM	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	-	110	500	μA			
Junction capacitance C _T		V _R = 200 V	-	9.0	14	pF			
Series inductance L _S		Measured lead to lead 5 mm from package body	-	8.0	-	nH			

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 $	A/μs, V _R = 30 V	-	26	-			
Reverse recovery time	t _{rr1}	T _J = 25 °C		-	53	80	ns		
	t _{rr2}	T _J = 125 °C		-	87	130			
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.4	8.0	A nC		
Feak recovery current	I _{RRM2}	T _J = 125 °C	l _F = 6.0 A dl _F /dt = 200 A/μs	-	5.0	9.0			
	Q _{rr1}	T _J = 25 °C	$V_{\rm R} = 200 \text{ V}$	-	116	320			
Reverse recovery charge	Q _{rr2}	T _J = 125 °C		-	233	585			
Peak rate of recovery current	dl _{(rec)M} /dt1	T _J = 25 °C	-		180	-	A/µs		
during t _b	dl _{(rec)M} /dt2	T _J = 125 °C]	-	100	-	λγμs		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	R _{thJC}		-	-	2.0				
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	K/W			
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-				
Weight			-	2.0	-	g			
weight			-	0.07	-	oz.			
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)			
Marking device		Case style TO-220AC		HFA06	STB120				

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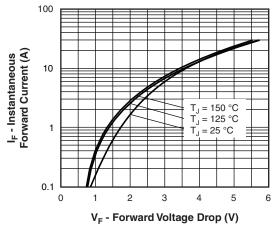
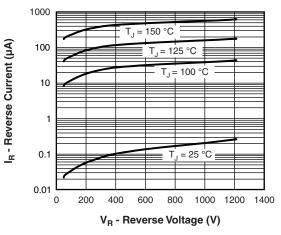
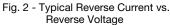


Fig. 1 - Typical Forward Voltage Drop Characteristics





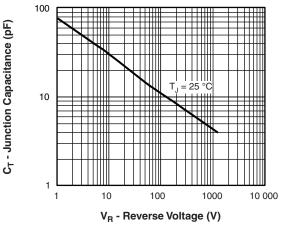
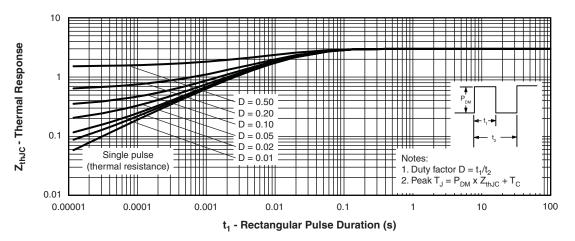
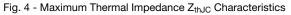


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage





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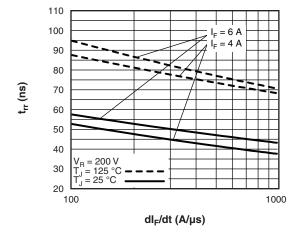


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

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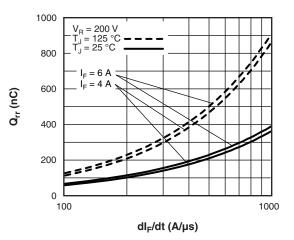


Fig. 7 - Typical Stored Charge vs. dl_F/dt

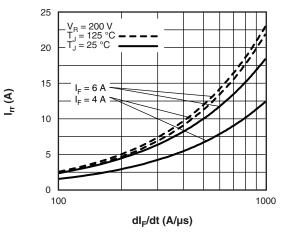


Fig. 6 - Typical Recovery Current vs. dI_F/dt

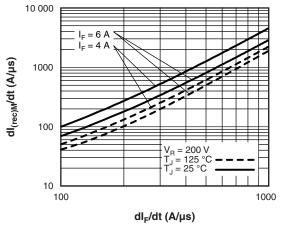


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

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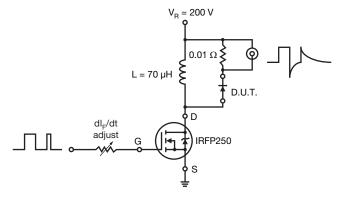


Fig. 9 - Reverse Recovery Parameter Test Circuit

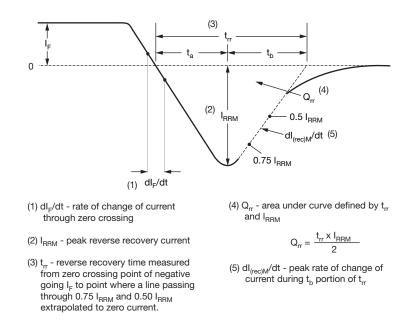


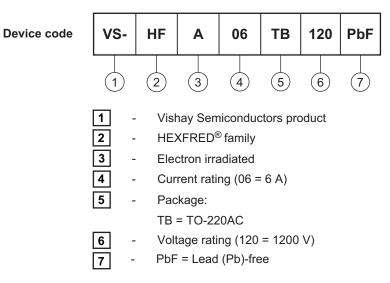
Fig. 10 - Reverse Recovery Waveform and Definitions



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ORDERING INFORMATION TABLE



Tube standard pack quantity: 50 pieces

LINKS TO RELATED DOCUMENTS								
Dimensions	www.vishay.com/doc?95221							
Part marking information	www.vishay.com/doc?95224							

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Vishay Semiconductors

TO-220AC

plane

DIMENSIONS in millimeters and inches









Diodes 1 + 2 - Cathode 3 - Anode

Conforms to JEDEC outline TO-220AC

⊕ 0.015 **()** BA()

SYMBOL	MILLIN	IETERS	INC	HES	NOTES	SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STIVIDOL	MIN.	MAX.	MIN.	MAX.	NOTES	OTMODE	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183		E1	6.86	8.89	0.270	0.350	6
A1	1.14	1.40	0.045	0.055		E2	-	0.76	-	0.030	7
A2	2.56	2.92	0.101	0.115		е	2.41	2.67	0.095	0.105	
b	0.69	1.01	0.027	0.040		e1	4.88	5.28	0.192	0.208	
b1	0.38	0.97	0.015	0.038	4	H1	6.09	6.48	0.240	0.255	6, 7
b2	1.20	1.73	0.047	0.068		L	13.52	14.02	0.532	0.552	
b3	1.14	1.73	0.045	0.068	4	L1	3.32	3.82	0.131	0.150	2
с	0.36	0.61	0.014	0.024		L3	1.78	2.13	0.070	0.084	
c1	0.36	0.56	0.014	0.022	4	L4	0.76	1.27	0.030	0.050	2
D	14.85	15.25	0.585	0.600	3	ØР	3.54	3.73	0.139	0.147	
D1	8.38	9.02	0.330	0.355		Q	2.60	3.00	0.102	0.118	
D2	11.68	12.88	0.460	0.507	6	θ	90° t	o 93°	90° t	o 93°	
E	10.11	10.51	0.398	0.414	3, 6						

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- ⁽⁴⁾ Dimension b1, b3 and c1 apply to base metal only
- ⁽⁵⁾ Controlling dimension: inches
- ⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2 and E1
- ⁽⁷⁾ Dimension E2 x H1 define a zone where stamping and singulation irregularities are allowed
- ⁽⁸⁾ Outline conforms to JEDEC TO-220, D2 (minimum) where dimensions are derived from the actual package outline



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